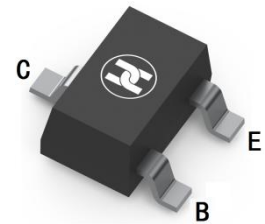
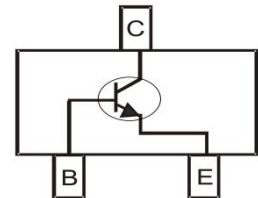


BIPOLAR TRANSISTOR (NPN)
FEATURES

- High Gain
- Low Collector Capacitance
- Surface Mount device


SOT-323
MECHANICAL DATA

- Case: SOT-323
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Weight: 0.008 grams (approximate)


MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	40	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	50	mA
Collector Power Dissipation	P _C	200	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	625	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~+150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Collector-base breakdown voltage	V _{(BR)CBO}	40			V	I _C =50μA, I _E =0
Collector-emitter breakdown voltage	V _{(BR)CEO}	25			V	I _C =1mA, I _B =0
Emitter-base breakdown voltage	V _{(BR)EBO}	5			V	I _E =50μA, I _C =0
Collector cut-off current	I _{CB0}			0.5	μA	V _{CB} =24V, I _E =0
Emitter cut-off current	I _{EBO}			0.5	μA	V _{EB} =3V, I _C =0
DC current gain	h _{FE}	56		270		V _{CE} =6V, I _C =1mA
Collector-emitter saturation voltage	V _{CE(sat)}			0.3	V	I _C =10mA, I _B =1mA
Transition frequency	f _T	150			MHz	V _{CE} =6V, I _C =1mA, f=100MHz
Collector output capacitance	C _{ob}			2.2	pF	V _{CE} =6V, I _E =0, f=1MHz

CLASSIFICATION OF h_{FE}

Rank	N	P	Q
Range	56-120	82-180	120-270
Marking	AN	AP	AQ

BIPOLAR TRANSISTOR (NPN)

Typical Characteristics

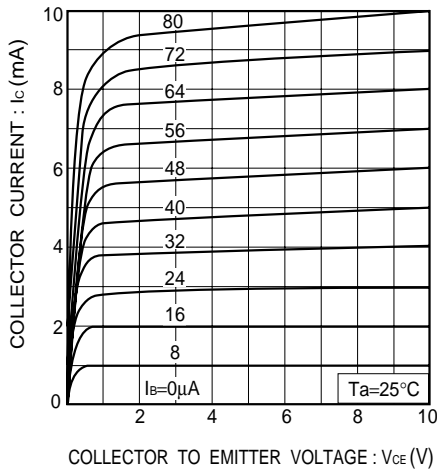


Fig.1 Ground emitter output characteristics

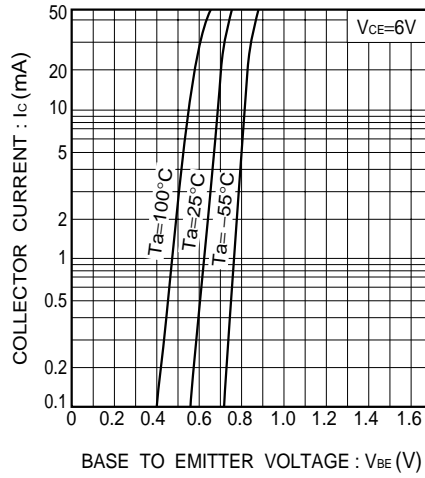


Fig.2 Ground emitter propagation characteristics

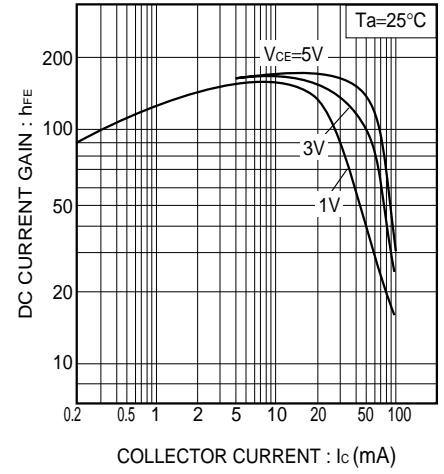


Fig.3 DC current gain vs. collector current (I)

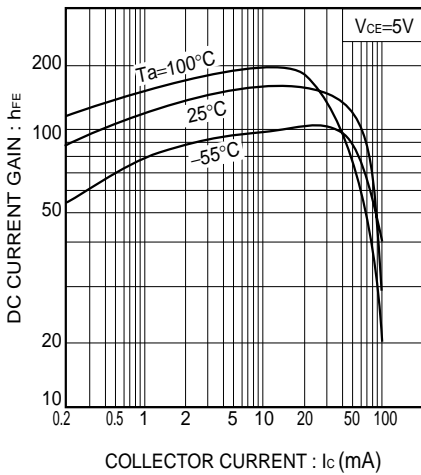


Fig.4 DC current gain vs. collector current (II)

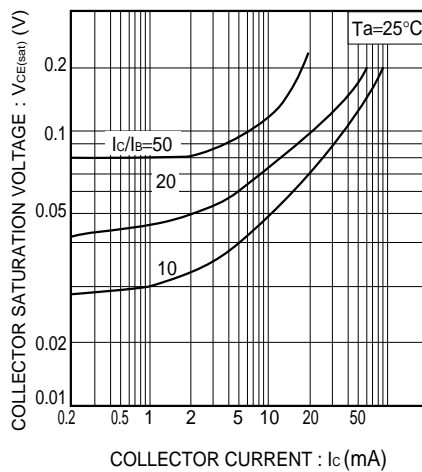


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

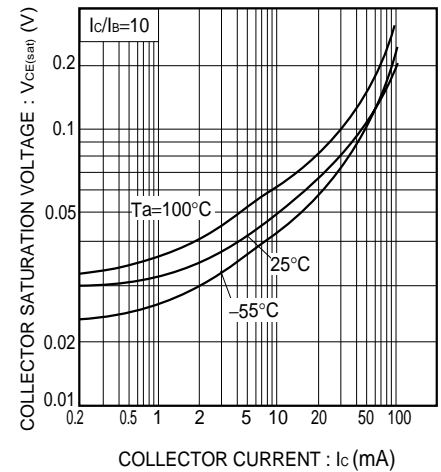


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

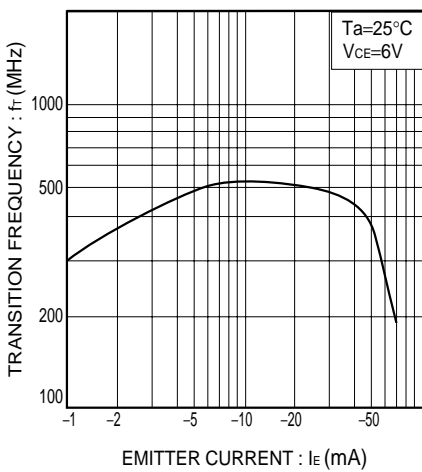


Fig.7 Gain bandwidth product vs. emitter current

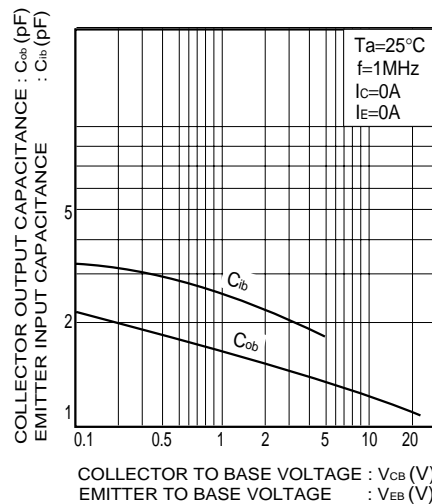


Fig.8 Capacitance vs. voltage

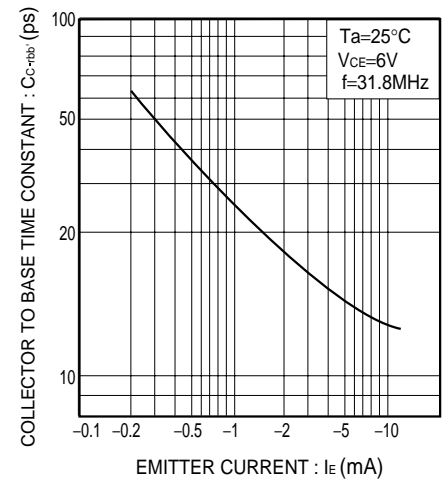
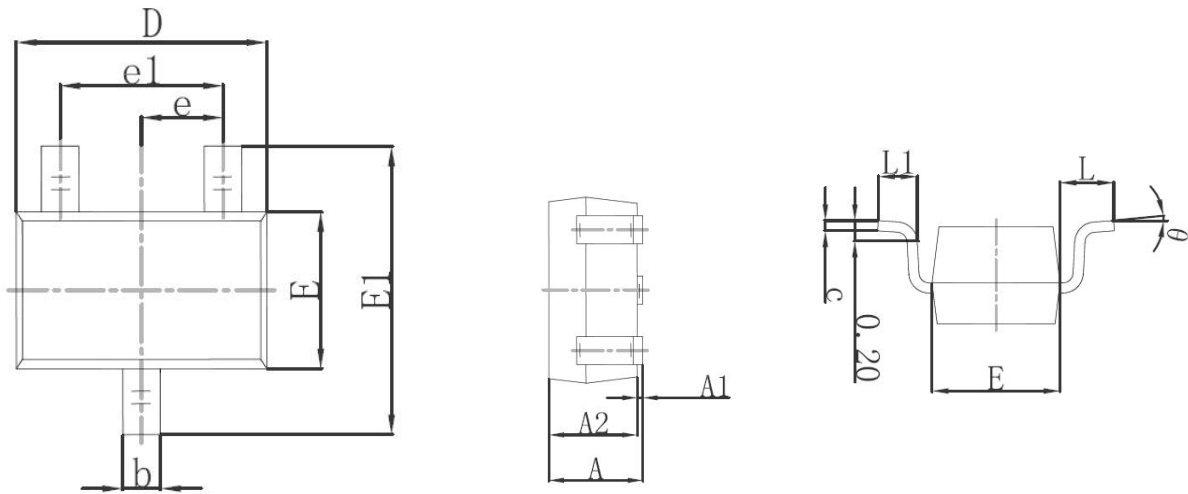


Fig.9 Collector to base time constant vs. emitter current

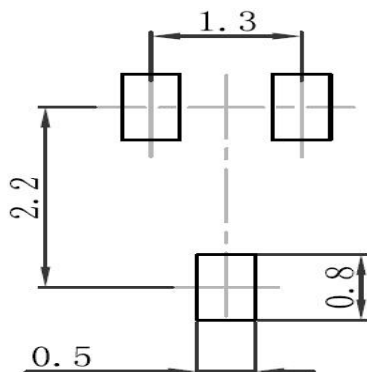
BIPOLAR TRANSISTOR (NPN)

SOT-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L	0.525REF		0.021REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-323 Suggested Pad Layout



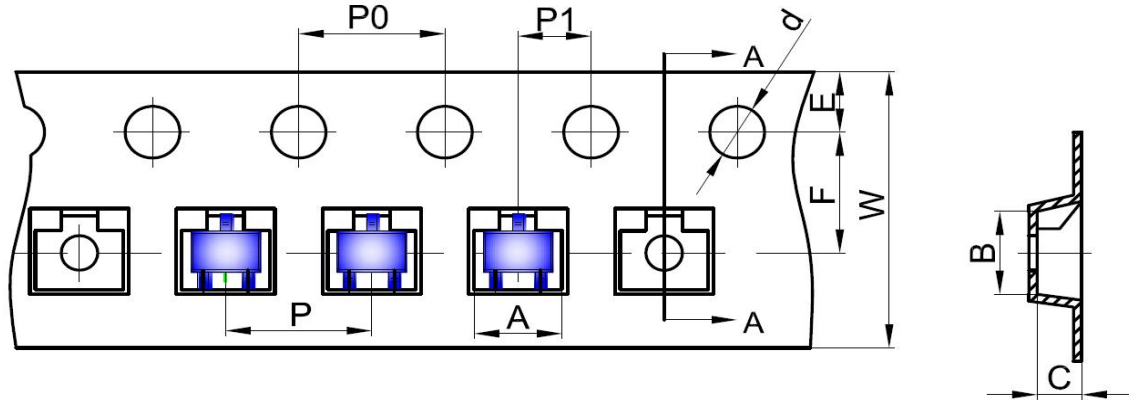
Note:

1. Controlling dimension: in millimeters
2. General tolerance: ±0.05mm
3. The pad layout is for reference purposes only

BIPOLAR TRANSISTOR (NPN)

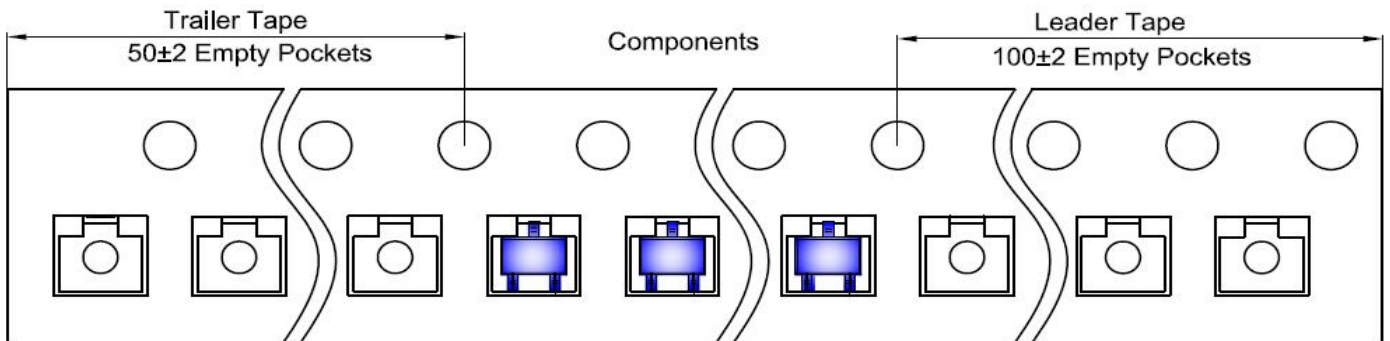
SOT-323 Tape and Reel

SOT-323 Embossed Carrier Tape

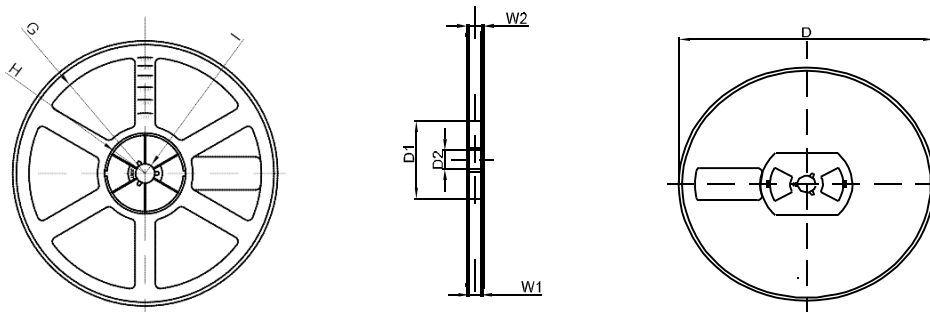


DIMENSIONS ARE IN MILLIMETER										
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-323	2.25	2.55	1.19	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

SOT-323 Tape Leader and Trailer



SOT-323 Reel



DIMENSIONS ARE IN MILLIMETER								
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1